

Regarding the prior art rejections of record, none of the cited references, either alone or in combination, teach or suggest the subject matter of the claims. Furthermore, the claims are believed sufficiently definite to allow one of ordinary skill in the art to know the metes and bounds of the claims.

### THE CLAIMED INVENTION

The claimed invention, as described in claim 1, is directed to *inter alia* a light-emitting apparatus that comprises a primary light source including a GaN semiconductor light-emitting device with an emission wavelength of from 380 nm to 500 nm, and a secondary light source including a fluorescent material including at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; and Y<sub>2</sub>O<sub>2</sub>S:Ce, in which the secondary light source emits light based on light given from the primary light source so that light of the secondary light source and the light of the primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from the primary light source, and in which the GaN semiconductor light-emitting device comprises a substrate, a light-emitting layer configured to emit light, and a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction.

The claimed invention, as described in claim 11, is directed to a light-emitting apparatus that comprises a primary light source including a GaN semiconductor light-emitting device with an emission wavelength of from 380 nm to 500 nm, and a secondary light source including a fluorescent material including at least one of ZnS:Eu and Y<sub>2</sub>O<sub>2</sub>S:Ce, in which the secondary light source emits light based on light given from the primary light source so that light of the secondary light source and the light of the primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from the primary light source, and in which the GaN semiconductor light-emitting device comprises a substrate, a light-emitting layer configured to emit light, and a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction.

The claimed invention, as described in claim 21, is directed to a light-emitting apparatus

that comprises a first light source including a GaN semiconductor light-emitting device configured to emit blue light, a second light source including a first fluorescent material configured to absorb light of the first light source and to emit green light, and a third light source including a second fluorescent material configured to absorb light of the first light source and to emit red light, in which the light of the first light source, light of the second light source, and light of the third light source are mixed together to thereby generate white light.

### CONCLUSION

In view of the foregoing, Applicants submit that claims 1-22, 25-34, and 38-40 all the claims presently pending in the application, are patentably distinct over the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Attorney's Deposit Account No. 50-0481.

Respectfully Submitted,

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS:**

**Please cancel claims 23, 24, 35, and 36 without prejudice or disclaimer.**

**Please amend claims 1, 11, 21, and 22 as follows:**

1. (Three Times Amended) A light-emitting apparatus comprising:
  - a primary light source including a GaN semiconductor light-emitting device with an emission wavelength of from 380 nm to 500 nm; and
  - a secondary light source including a fluorescent material including at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; and Y<sub>2</sub>O<sub>2</sub>S:Ce[; and
  - a third light source configured to emit red light],wherein said secondary light source emits light based on light given from said primary light source so that light of said secondary light source and the light of said primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source, and
  - wherein the GaN semiconductor light-emitting device comprises:
    - a substrate;
    - a light-emitting layer configured to emit light; and
    - a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction.
11. (Three Times Amended) A light-emitting apparatus comprising:
  - a primary light source including a GaN semiconductor light-emitting device with an emission wavelength of from [420] 380 nm to [490] 500 nm; and
  - a secondary light source including a [first] fluorescent material [composed of] including at least one [member selected from the group consisting] of ZnS:Eu[, YVO<sub>4</sub>:Ce] and Y<sub>2</sub>O<sub>2</sub>S:Ce[; and
  - a third light source including a second fluorescent material configured to absorb the light of said primary light source, the third light source being configured to emit red light],

wherein said secondary light source emits light based on light given from said primary light source so that light of said secondary light source and the light of said primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source, and

wherein the GaN semiconductor light-emitting device comprises:

a substrate;

a light-emitting layer configured to emit light; and

a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction.

21. (Three Times Amended) A light-emitting apparatus comprising:

a first light source including a GaN semiconductor light-emitting device configured to emit blue light;

a second light source including a first fluorescent material configured to absorb light of said first light source and to emit green light; and

a third light source [comprising a red color LED] including a second fluorescent material configured to absorb light of said first light source and to emit red light[;],

wherein the light of said first light source, light of said second light source, and light of said third light source are mixed together to thereby generate white light[, and

wherein the GaN semiconductor light-emitting device comprises:

a substrate;

a light-emitting layer configured to emit light; and

a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction].

22. (Twice Amended) A light-emitting apparatus according to claim 21, wherein said first fluorescent material [is composed of] comprises at least one [member selected from the

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group consisting] of ZnS:Cu, Au, Al; ZnS:Cu; ZnS:Mn; ZnS:Eu; [YV O<sub>4</sub>:Ce;] Y<sub>2</sub> O<sub>2</sub>S:Eu<sub>1</sub> and Y<sub>2</sub> O<sub>2</sub>S:Ce.